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## Corrigendum: Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy

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As the authors of references 25 and 26 also employed plasma-assisted molecular beam epitaxy for the synthesis of hexagonal boron nitride films, the authors would like to make the following changes to the Introduction section of their Article:

“In addition the direct growth of hBN on a two-dimensional material (HOPG) offers an alternative to chemical vapour deposition<sup>23,24,25,26</sup> and atomic layer deposition<sup>27</sup> of hBN on metal substrates; this approach must typically be complemented by complex protocols for the removal and transfer of the grown films”.

Should read:

“In addition the direct growth of hBN on a two-dimensional material (HOPG) offers an alternative to chemical vapour deposition<sup>23,24</sup>, MBE<sup>25,26</sup> and atomic layer deposition<sup>27</sup> of hBN on metal substrates; this approach must typically be complemented by complex protocols for the removal and transfer of the grown films”.



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